



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	Rds(on) max	ID MAX TC = +25°C
700V	$1.4\Omega @ V_{GS} = 10V$	4.7A

Description

This new generation MOSFET is designed to minimize the on-state resistance (RDS(ON)) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Adaptor
- LCD & PDP TV
- Lighting

Features

- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low Gate Input Resistance
- Low Input Capacitance
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

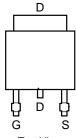
Mechanical Data

- Case: TO252
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (63)
- Weight: 0.33 grams (Approximate)

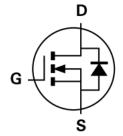




Top View



Top View



Internal Schematic

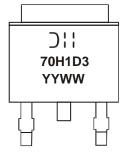
Ordering Information (Note 4)

Part Number	Compliance	Case	Packaging
DMJ70H1D3SK3-13	Standard	TO252 (DPAK)	2,500/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



☐ I = Manufacturer's Marking 70H1D3 = Product Type Marking Code YYWW = Date Code Marking YY or YY = Last Two Digits of Year (ex. 20 = 2020) WW or WW = Week Code (01 to 53)



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	700	V	
Gate-Source Voltage	Vgss	±30	V	
Continuous Drain Current (Notes 5 & 9) $V_{GS} = 10V$ $T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$		lo	4.7 3.0	А
Maximum Body Diode Forward Current (Note 6)	•	Is	2	A
Pulsed Source Current (10µs Pulse, Duty Cycle = 1%)	Ism	5	A	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	5	A	
Avalanche Current, L = 60mH	las	1	A	
Avalanche Energy, L = 60mH	Eas	29	mJ	
Peak Diode Recovery dv/dt (Note 7)		dv/dt	4	V/ns

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

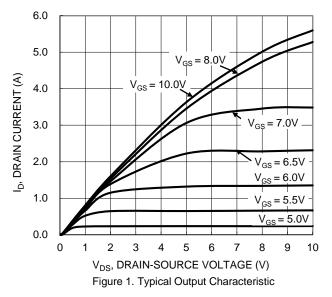
Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	T _C = +25°C	Pp	57	- W
Total Fower Dissipation (Note 3)	T _C = +100°C	רט	23	
Thermal Resistance, Junction to Ambient (Note 6)	Reja	80	°C/W	
Thermal Resistance, Junction to Case (Note 5)	Rejc	2.2	- C/VV	
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C	

Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	700	_	_	V	$V_{GS} = 0V, I_{D} = 250\mu A$	
Zero Gate Voltage Drain Current	IDSS	_	_	1	μA	V _{DS} = 700V, V _{GS} = 0V	
Gate-Source Leakage	Igss	_	_	100	nA	Vgs = ±30V, Vps = 0V	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(TH)}	2	_	5	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	RDS(ON)	_	1.26	1.4	Ω	VGS = 10V, ID = 1A	
Diode Forward Voltage	VsD	_	_	1.3	V	V _G S = 0V, I _S = 5A	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	Ciss	_	264	_		V _{DS} = 100V, f = 1MHz, V _{GS} = 0V	
Output Capacitance	Coss		18		pF		
Reverse Transfer Capacitance	Crss	_	2.8	_			
Gate Resistance	Rg	_	4.7	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Qg	_	9.8	_		V _{DD} = 480V, I _D = 1.5A,	
Gate-Source Charge	Qgs	_	1.7	_	nC		
Gate-Drain Charge	Qgd	_	6	_		Vgs = 10V	
Turn-On Delay Time	t _{D(ON)}	_	9	_		$V_{DD} = 400V, V_{GS} = 13V,$ $R_g = 10.2\Omega, I_D = 1.5A$	
Turn-On Rise Time	t _R	_	11	_	ns		
Turn-Off Delay Time	tD(OFF)	_	31	_	115		
Turn-Off Fall Time	tF	_	19	_			
Body Diode Reverse Recovery Time	t _{RR}	_	145	_	ns	1 4 50 4:/44 4000/	
Body Diode Reverse Recovery Charge	Q _{RR}	_	0.8	_	μC	$I_S = 1.5A$, di/dt = 100A/ μ s	

- 5. Device mounted on an infinite heatsink.
- Device mounted on FR-4 substrate PC board, 2oz. copper, with minimum recommended pad layout.
 Guaranteed by design. Not subject to production testing.
 Short duration pulse test used to minimize self-heating effect.
 Drain current limited by maximum junction temperature.





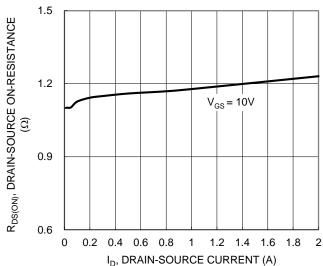


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

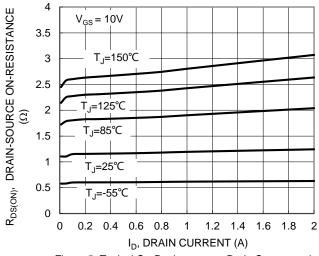


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

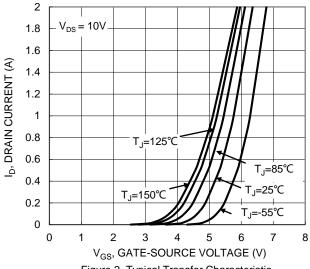


Figure 2. Typical Transfer Characteristic

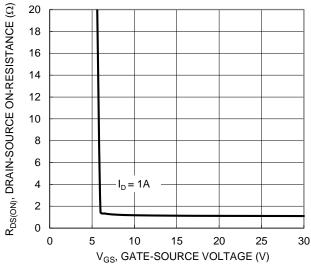


Figure 4. Typical Transfer Characteristic

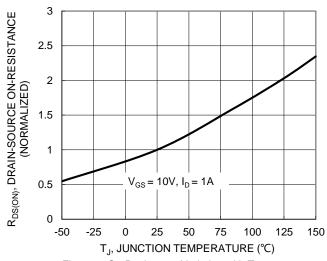


Figure 6. On-Resistance Variation with Temperature





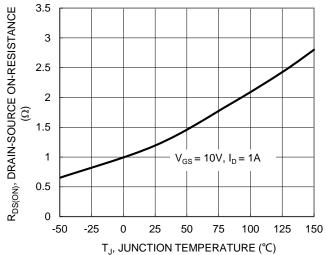


Figure 7. On-Resistance Variation with Temperature

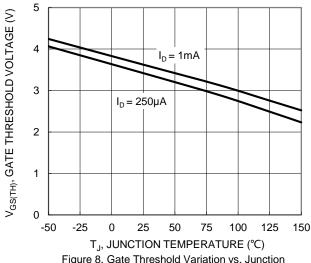


Figure 8. Gate Threshold Variation vs. Junction Temperature

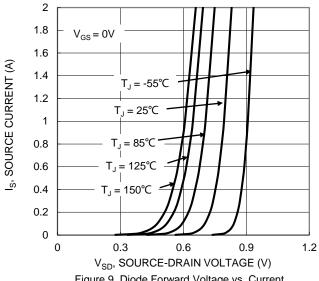
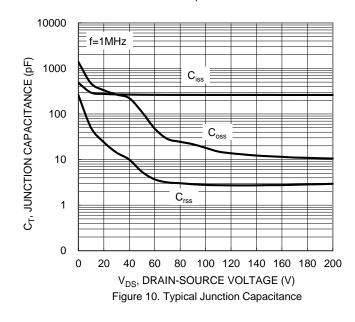
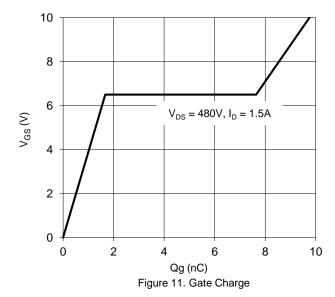


Figure 9. Diode Forward Voltage vs. Current





10 R_{DS(ON)} Limited **DRAIN CURRENT (A)** $P_W = 10 \mu s$ 0.1 $T_{J(Max)} = 150^{\circ}C$ $T_C = 25^{\circ}C$ م_ $P_W = 10 ms$ Single Pulse **DUT** on Infinite Heatsink $V_{GS} = 10V$ 0.01 100 V_{DS}, DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area



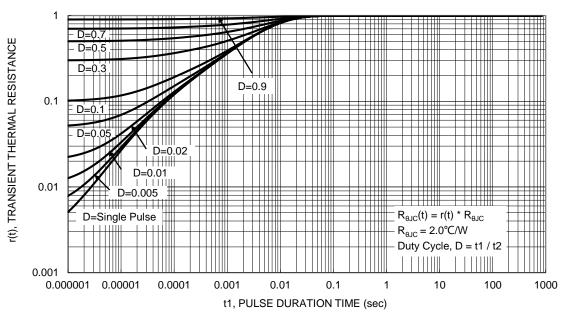


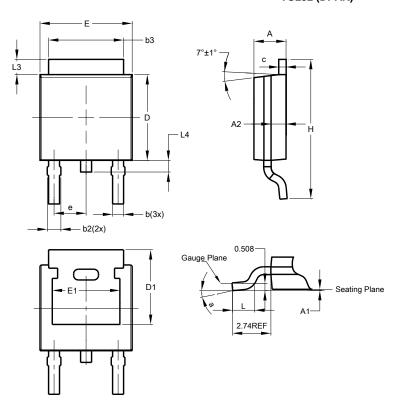
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)

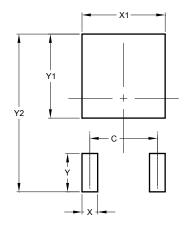


TO252 (DPAK)					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
A1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
b	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
С	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	-	-		
е	-	-	2.286		
Е	6.45	6.70	6.58		
E1	4.32	-	-		
Н	9.40	10.41	9.91		
L	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	-		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)			
С	4.572			
X	1.060			
X1	5.632			
Υ	2.600			
Y1	5.700			
Y2	10.700			



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